

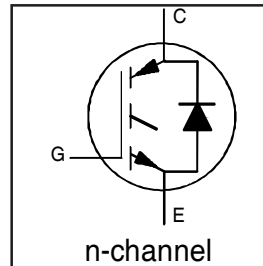
IRG4IBC20KDPbF

INSULATED GATE BIPOLAR TRANSISTOR WITH
ULTRAFAST SOFT RECOVERY DIODE

Short Circuit Rated
UltraFast IGBT

Features

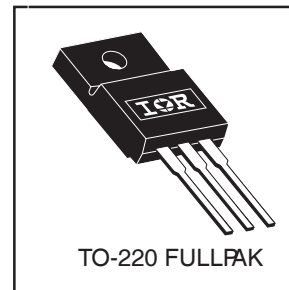
- High switching speed optimized for up to 25kHz with low $V_{CE(on)}$
- Short Circuit Rating 10 μ s @ 125°C, $V_{GE} = 15V$
- Generation 4 IGBT design provides tighter parameter distribution and higher efficiency than previous generation
- IGBT co-packaged with HEXFRED™ ultrafast, ultra-soft-recovery anti-parallel diodes for use in bridge configurations
- Industry standard TO-220 FULLPAK
- Lead-Free



$V_{CES} = 600V$
$V_{CE(on)} \text{ typ.} = 2.27V$
@ $V_{GE} = 15V, I_C = 6.3A$

Benefits

- Generation 4 IGBTs offer highest efficiencies available maximizing the power density of the system
- IGBTs optimized for specific application conditions
- HEXFRED™ diodes optimized for performance with IGBTs. Minimized recovery characteristics reduce noise EMI
- Designed to exceed the power handling capability of equivalent industry-standard IGBTs



Absolute Maximum Ratings

	Parameter	Max.	Units
V_{CES}	Collector-to-Emitter Voltage	600	V
$I_C @ T_C = 25^\circ C$	Continuous Collector Current	11.5	A
$I_C @ T_C = 100^\circ C$	Continuous Collector Current	6.3	
I_{CM}	Pulsed Collector Current ①	23	
I_{LM}	Clamped Inductive Load Current ②	23	
$I_F @ T_C = 100^\circ C$	Diode Continuous Forward Current	6.3	
I_{FM}	Diode Maximum Forward Current	23	
t_{sc}	Short Circuit Withstand Time	10	μ s
V_{ISOL}	RMS Isolation Voltage, Terminal to Case, $t = 1 \text{ min}$	2500	V
V_{GE}	Gate-to-Emitter Voltage	± 20	
$P_D @ T_C = 25^\circ C$	Maximum Power Dissipation	34	W
$P_D @ T_C = 100^\circ C$	Maximum Power Dissipation	14	
T_J	Operating Junction and	-55 to +150	$^\circ C$
T_{STG}	Storage Temperature Range		
	Soldering Temperature, for 10 sec.	300 (0.063 in. (1.6mm) from case)	
	Mounting Torque, 6-32 or M3 Screw.	10 lbf•in (1.1 N•m)	

Thermal Resistance

	Parameter	Typ.	Max.	Units
$R_{\theta JC}$	Junction-to-Case - IGBT	---	3.7	$^\circ C/W$
$R_{\theta CS}$	Junction-to-Case - Diode	---	5.5	
$R_{\theta JA}$	Junction-to-Ambient, typical socket mount	---	65	
Wt	Weight	2.0 (0.07)	---	g (oz)

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Electrical Characteristics @ $T_J = 25^\circ\text{C}$ (unless otherwise specified)

	Parameter	Min.	Typ.	Max.	Units	Conditions	
$V_{(BR)CES}$	Collector-to-Emitter Breakdown Voltage ^③	600	—	—	V	$V_{GE} = 0V, I_C = 250\mu A$	
$\Delta V_{(BR)CES}/\Delta T_J$	Temperature Coeff. of Breakdown Voltage	—	0.49	—	V/ $^\circ\text{C}$	$V_{GE} = 0V, I_C = 1.0mA$	
$V_{CE(on)}$	Collector-to-Emitter Saturation Voltage	—	2.27	2.8	V	$I_C = 9.0A$ $I_C = 16A$ $I_C = 9.0A, T_J = 150^\circ\text{C}$	
		—	3.01	—			$V_{GE} = 15V$
		—	2.43	—			See Fig. 2, 5
$V_{GE(th)}$	Gate Threshold Voltage	3.0	—	6.0		$V_{CE} = V_{GE}, I_C = 250\mu A$	
$\Delta V_{GE(th)}/\Delta T_J$	Temperature Coeff. of Threshold Voltage	—	-10	—	mV/ $^\circ\text{C}$	$V_{CE} = V_{GE}, I_C = 250\mu A$	
g_{fe}	Forward Transconductance ^④	2.9	4.3	—	S	$V_{CE} = 100V, I_C = 9.0A$	
I_{CES}	Zero Gate Voltage Collector Current	—	—	250	μA	$V_{GE} = 0V, V_{CE} = 600V$ $V_{GE} = 0V, V_{CE} = 600V, T_J = 150^\circ\text{C}$	
		—	—	1000			
V_{FM}	Diode Forward Voltage Drop	—	1.4	1.7	V	$I_C = 8.0A$ $I_C = 8.0A, T_J = 150^\circ\text{C}$	
		—	1.3	1.6			See Fig. 13
I_{GES}	Gate-to-Emitter Leakage Current	—	—	± 100	nA	$V_{GE} = \pm 20V$	

Switching Characteristics @ $T_J = 25^\circ\text{C}$ (unless otherwise specified)

	Parameter	Min.	Typ.	Max.	Units	Conditions	
Q_g	Total Gate Charge (turn-on)	—	34	51	nC	$I_C = 9.0A$ $V_{CC} = 400V$ $V_{GE} = 15V$	
Q_{ge}	Gate - Emitter Charge (turn-on)	—	4.9	7.4			See Fig. 8
Q_{gc}	Gate - Collector Charge (turn-on)	—	14	21			
$t_{d(on)}$	Turn-On Delay Time	—	54	—	ns	$T_J = 25^\circ\text{C}$ $I_C = 9.0A, V_{CC} = 480V$ $V_{GE} = 15V, R_G = 50\Omega$	
t_r	Rise Time	—	34	—			
$t_{d(off)}$	Turn-Off Delay Time	—	180	270			
t_f	Fall Time	—	72	110			
E_{on}	Turn-On Switching Loss	—	0.34	—	mJ	Energy losses include "tail" and diode reverse recovery See Fig. 9,10,14	
E_{off}	Turn-Off Switching Loss	—	0.30	—			
E_{ts}	Total Switching Loss	—	0.64	0.96			
t_{sc}	Short Circuit Withstand Time	10	—	—	μs	$V_{CC} = 360V, T_J = 125^\circ\text{C}$ $V_{GE} = 15V, R_G = 50\Omega, V_{CPK} < 500V$	
$t_{d(on)}$	Turn-On Delay Time	—	51	—	ns	$T_J = 150^\circ\text{C}$, See Fig. 10,11,14 $I_C = 9.0A, V_{CC} = 480V$ $V_{GE} = 15V, R_G = 50\Omega$	
t_r	Rise Time	—	37	—			
$t_{d(off)}$	Turn-Off Delay Time	—	220	—			
t_f	Fall Time	—	160	—			
E_{ts}	Total Switching Loss	—	0.85	—	mJ	Energy losses include "tail" and diode reverse recovery	
L_E	Internal Emitter Inductance	—	7.5	—	nH	Measured 5mm from package	
C_{ies}	Input Capacitance	—	450	—	pF	$V_{GE} = 0V$ $V_{CC} = 30V$ $f = 1.0MHz$	
C_{oes}	Output Capacitance	—	61	—			See Fig. 7
C_{res}	Reverse Transfer Capacitance	—	14	—			
t_{rr}	Diode Reverse Recovery Time	—	37	55	ns	$T_J = 25^\circ\text{C}$ See Fig. 14 $T_J = 125^\circ\text{C}$	
		—	55	90			$I_F = 8.0A$
I_{rr}	Diode Peak Reverse Recovery Current	—	3.5	5.0	A	$T_J = 25^\circ\text{C}$ See Fig. 15 $T_J = 125^\circ\text{C}$	
		—	4.5	8.0			$V_R = 200V$
Q_{rr}	Diode Reverse Recovery Charge	—	65	138	nC	$T_J = 25^\circ\text{C}$ See Fig. 16 $T_J = 125^\circ\text{C}$	
		—	124	360			$di/dt = 200A/\mu s$
$di_{(rec)M}/dt$	Diode Peak Rate of Fall of Recovery During t_b	—	240	—	A/ μs	$T_J = 25^\circ\text{C}$ See Fig. 17 $T_J = 125^\circ\text{C}$	
		—	210	—			

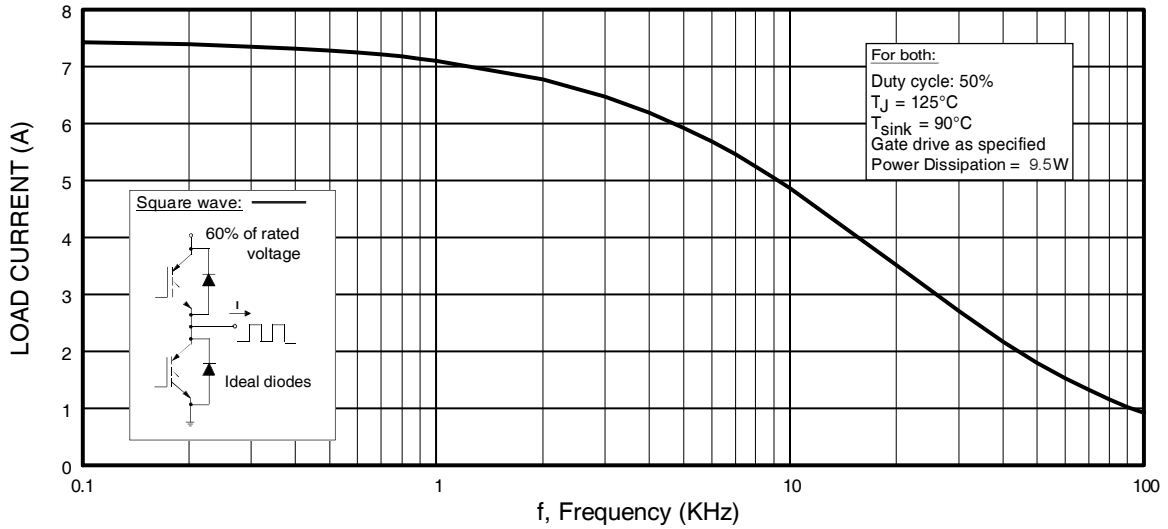


Fig. 1 - Typical Load Current vs. Frequency
 (Load Current = I_{RMS} of fundamental)

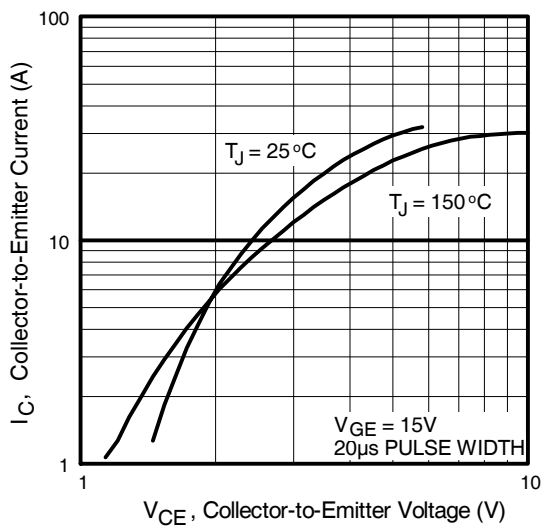


Fig. 2 - Typical Output Characteristics

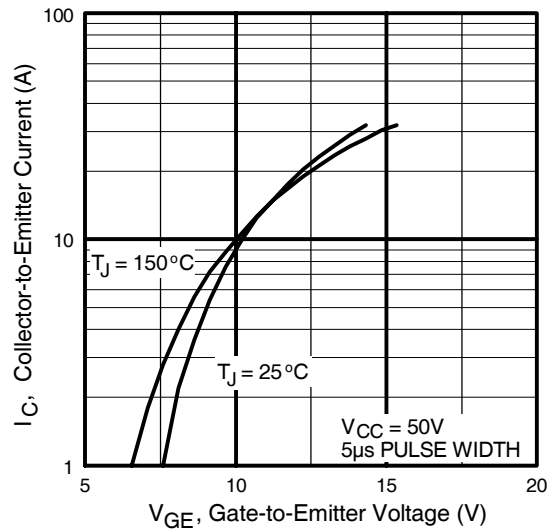


Fig. 3 - Typical Transfer Characteristics

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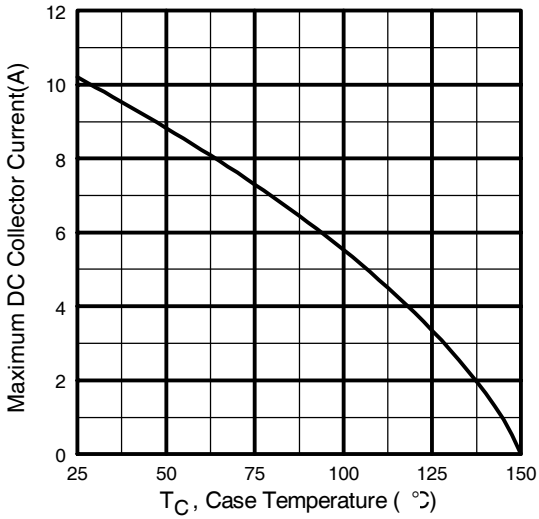


Fig. 4 - Maximum Collector Current vs. Case Temperature

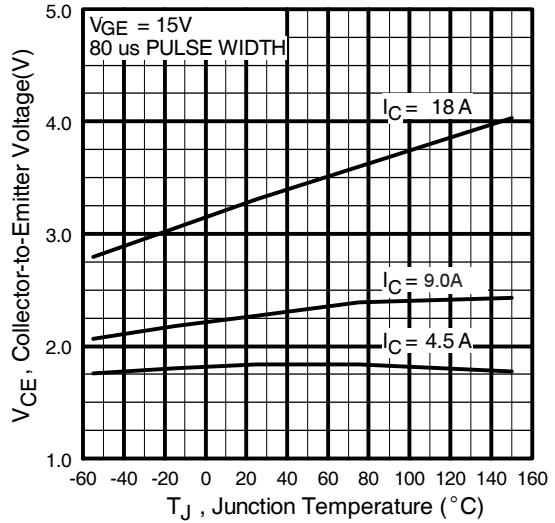


Fig. 5 - Typical Collector-to-Emitter Voltage vs. Junction Temperature

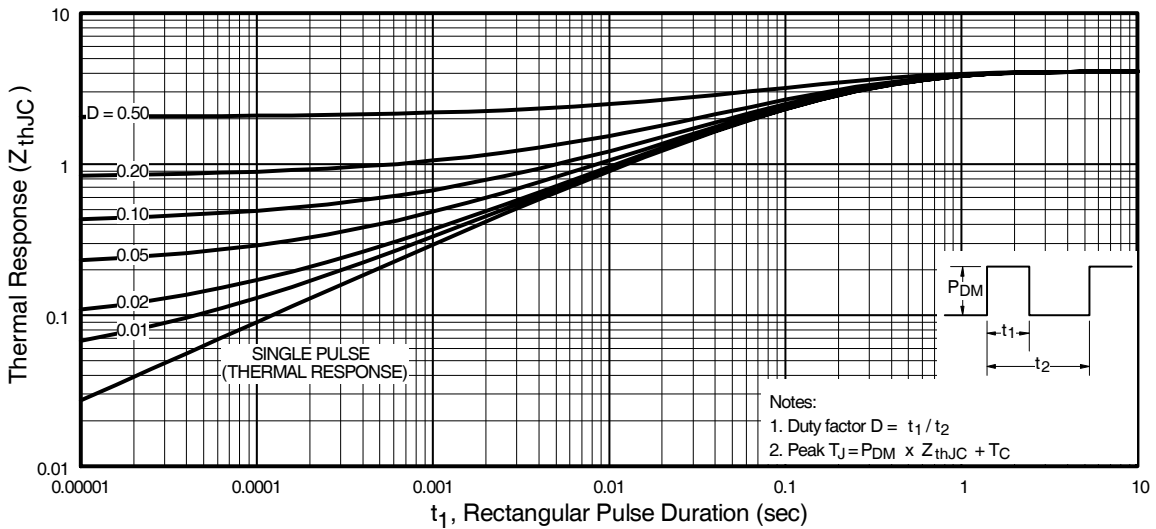


Fig. 6 - Maximum Effective Transient Thermal Impedance, Junction-to-Case

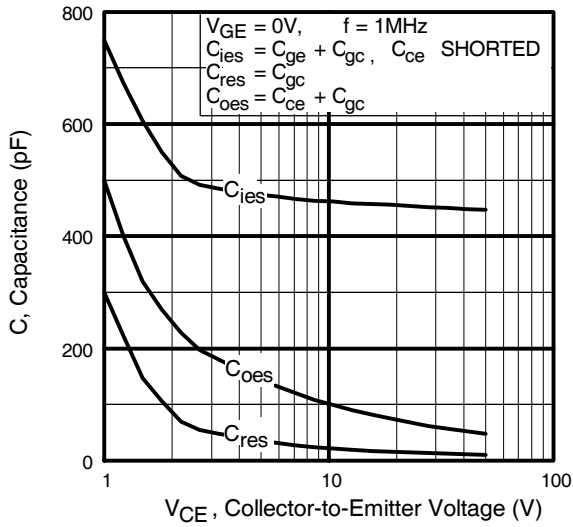


Fig. 7 - Typical Capacitance vs. Collector-to-Emitter Voltage

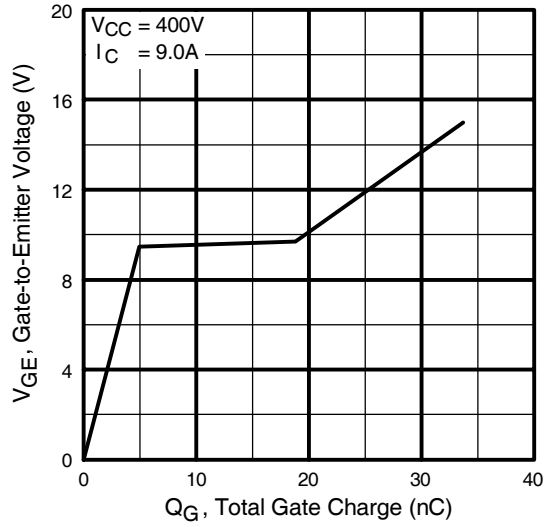


Fig. 8 - Typical Gate Charge vs. Gate-to-Emitter Voltage

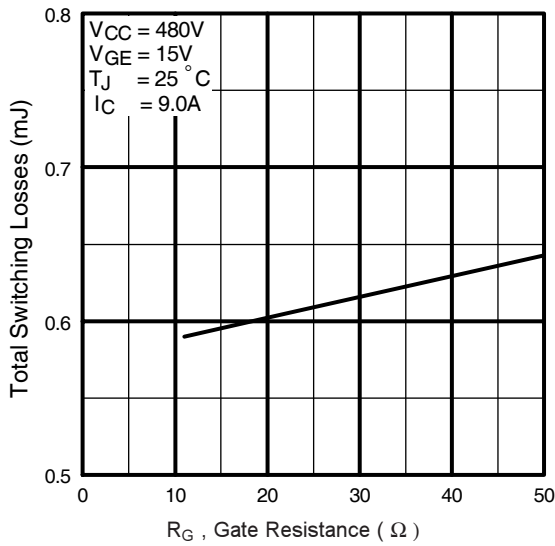


Fig. 9 - Typical Switching Losses vs. Gate Resistance

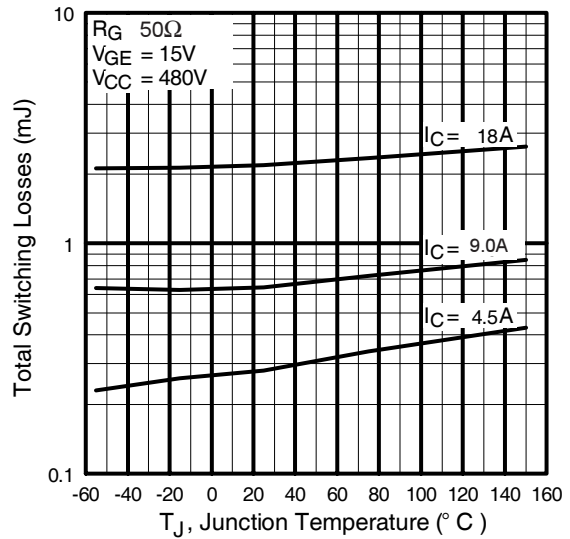


Fig. 10 - Typical Switching Losses vs. Junction Temperature

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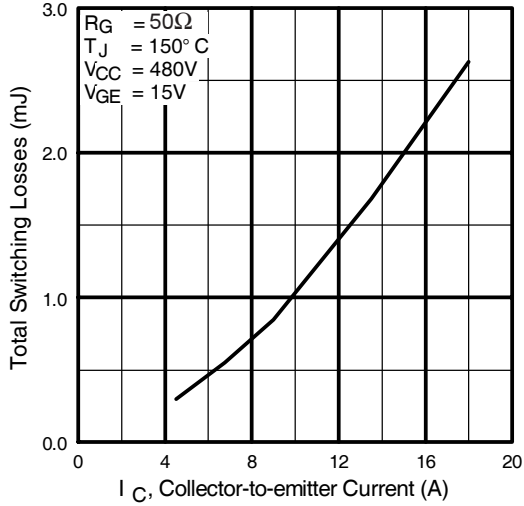


Fig. 11 - Typical Switching Losses vs. Collector-to-Emitter Current

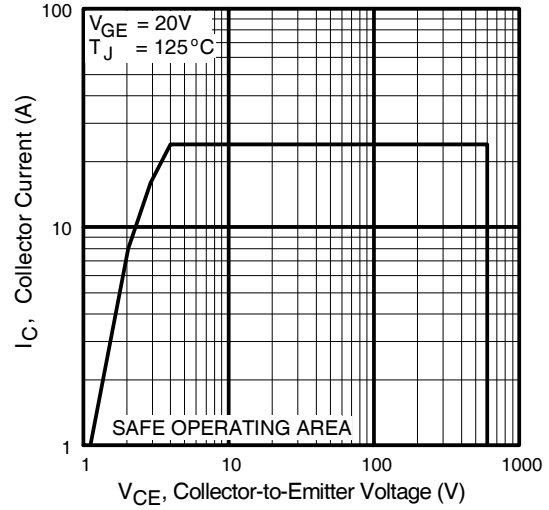


Fig. 12 - Turn-Off SOA

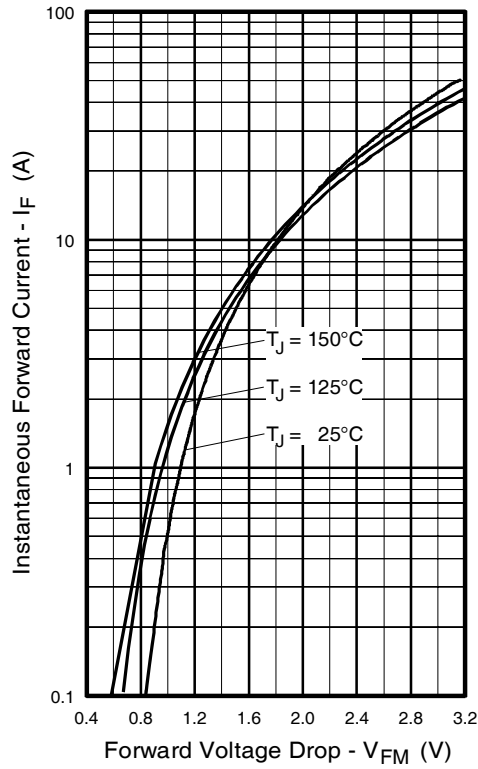


Fig. 13 - Maximum Forward Voltage Drop vs. Instantaneous Forward Current

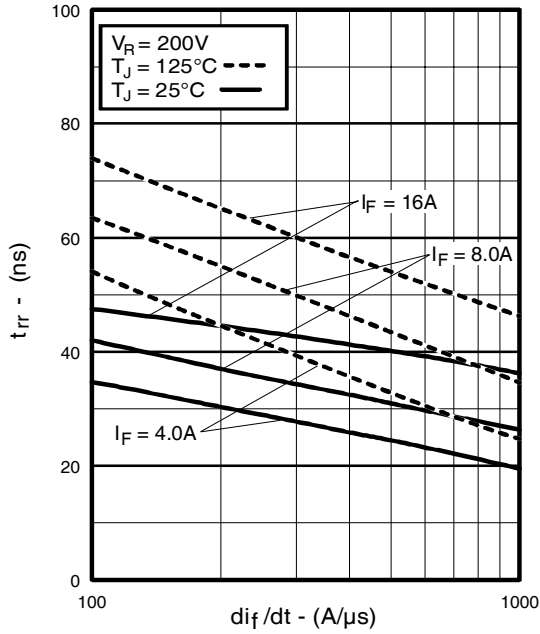


Fig. 14 - Typical Reverse Recovery vs. di_f/dt

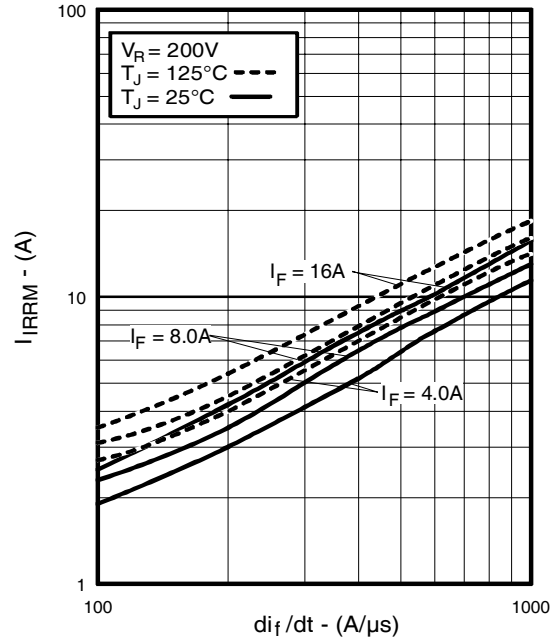


Fig. 15 - Typical Recovery Current vs. di_f/dt

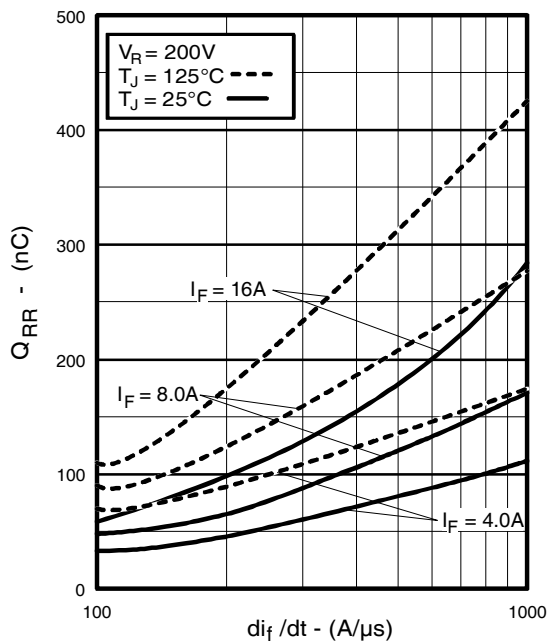


Fig. 16 - Typical Stored Charge vs. di_f/dt

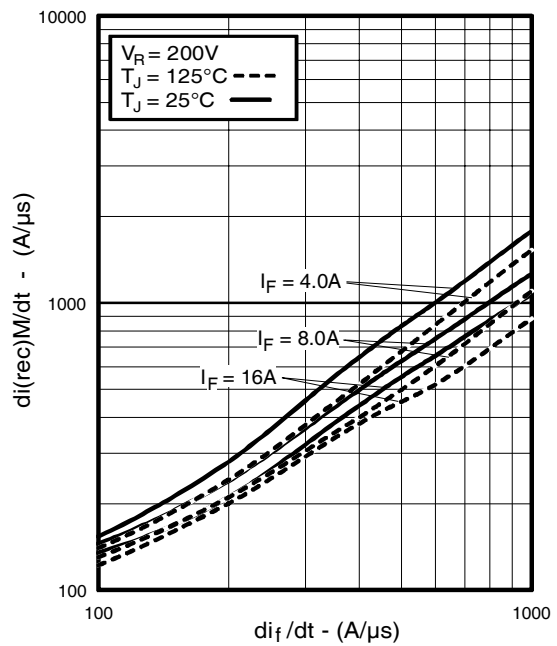


Fig. 17 - Typical $di(\text{rec})M/dt$ vs. di_f/dt

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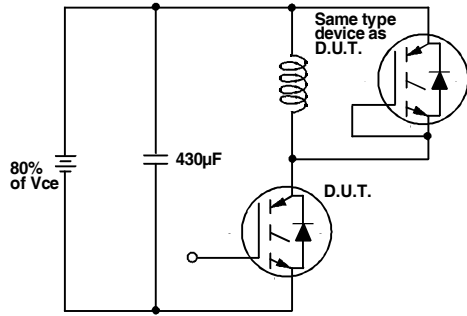


Fig. 18a - Test Circuit for Measurement of I_{LM} , E_{on} , $E_{off}(\text{diode})$, t_{rr} , Q_{rr} , I_{rr} , $t_{d(on)}$, t_r , $t_{d(off)}$, t_f

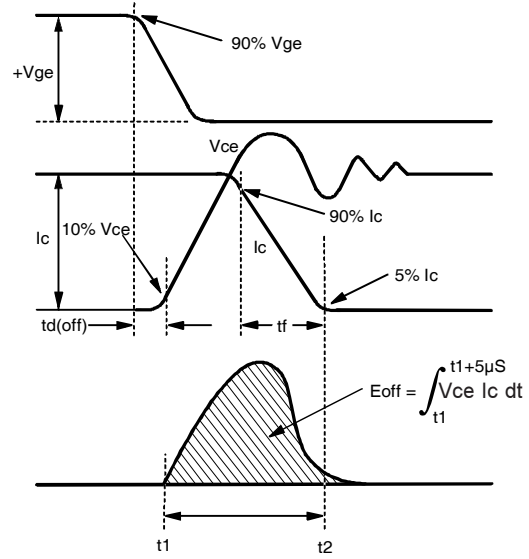


Fig. 18b - Test Waveforms for Circuit of Fig. 18a, Defining E_{off} , $t_{d(off)}$, t_f

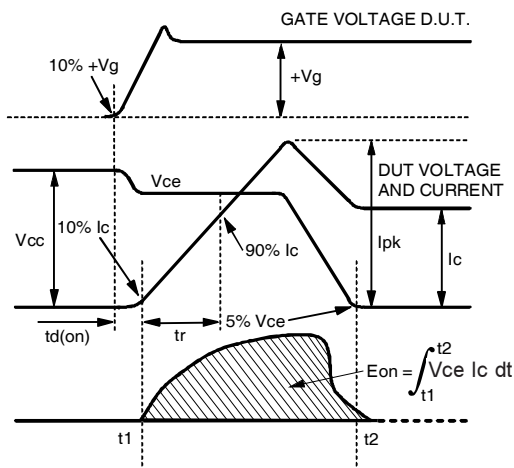


Fig. 18c - Test Waveforms for Circuit of Fig. 18a, Defining E_{on} , $t_{d(on)}$, t_r

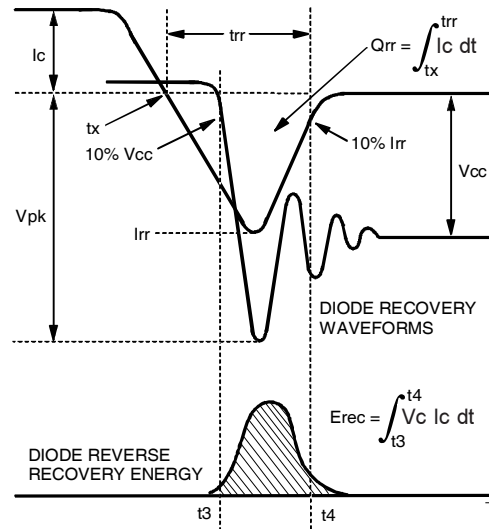


Fig. 18d - Test Waveforms for Circuit of Fig. 18a, Defining E_{rec} , t_{rr} , Q_{rr} , I_{rr}

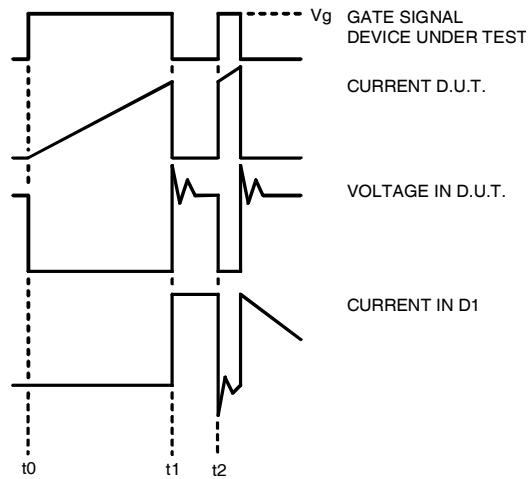


Figure 18e. Macro Waveforms for Figure 18a's Test Circuit

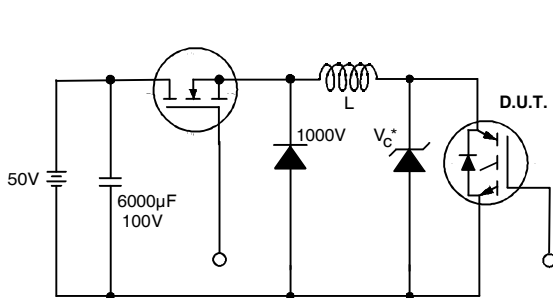


Figure 19. Clamped Inductive Load Test Circuit

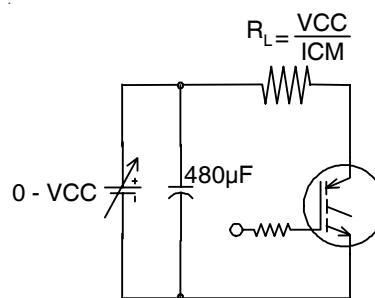


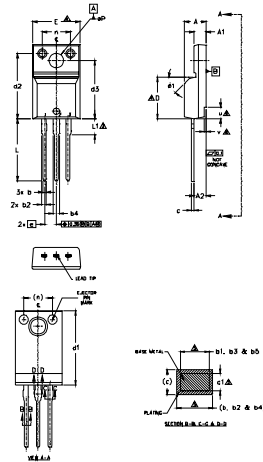
Figure 20. Pulsed Collector Current Test Circuit

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TO-220AB Full-Pak Package Outline

Dimensions are shown in millimeters (inches)



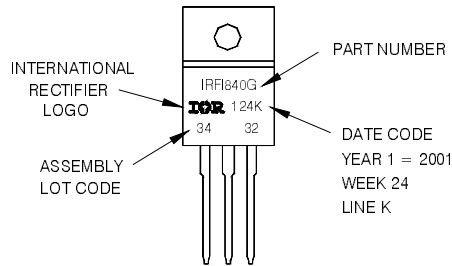
SYMBOL	DIMENSIONS				NOTES
	MILLIMETERS		INCHES		
	MIN.	MAX.	MIN.	MAX.	
A	4.57	4.83	.180	.190	
A1	2.57	2.83	.101	.111	
A2	2.51	2.93	.099	.115	
b	0.61	0.94	.024	.037	
b1	0.61	0.89	.024	.035	5
b2	0.76	1.27	.030	.050	
b3	0.76	1.22	.030	.048	5
b4	1.02	1.52	.040	.060	
b5	1.02	1.47	.040	.058	5
c	0.33	0.63	.013	.025	
c1	0.33	0.38	.013	.023	5
D	8.66	9.80	.341	.386	4
d1	15.80	16.13	.622	.635	
d2	13.97	14.22	.550	.560	
d3	12.30	12.93	.484	.509	
E	9.63	10.76	.379	.423	4
e	2.54 BSC		100 BSC		
L	13.20	13.72	.520	.540	3
L1	3.37	3.67	.122	.145	
n	6.05	6.60	.238	.260	
øP	3.05	3.45	.120	.136	
u	2.40	2.60	.094	.098	6
v	0.40	0.50	.016	.020	6
ø1	— 45°		— 45°		

NOTES
 1. DIMENSIONS AND TOLERANCING AS PER ASME Y14.5 M - 1994.
 2. DIMENSIONS ARE SHOWN IN MILLIMETERS (INCHES).
 3. LEAD DIMENSION AND FINISH UNCONTROLLED IN LT.
 4. DIMENSION D & E DO NOT INCLUDE WELD FLASH; WELD FLASH SHALL NOT EXCEED .002 (0.077) PER SIDE; THESE DIMENSIONS ARE MEASURED AT THE OUTER MOST EXTREMES OF THE PLASTIC BODY.
 5. DIMENSION H1, H2, H3 & H4 APPLY TO BARE METAL ONLY.
 6. STEP OPTIONAL ON PLASTIC BODY DEFINED BY DIMENSIONS A & A1.
 7. CONTROLLING DIMENSION - BONES.
 LEAD ASSIGNMENTS
 1. GATE
 2. DRAIN
 3. SOURCE
 LABEL CODES
 1. GATE
 2. COLLECTOR
 3. EMITTER

TO-220AB Full-Pak Part Marking Information

EXAMPLE: THIS IS AN IRF1840G
 WITH ASSEMBLY
 LOT CODE 3432
 ASSEMBLED ON WW 24, 2001
 IN THE ASSEMBLY LINE 'K'

Note: 'P' in assembly line position
 indicates 'Lead-Free'



TO-220AB Full-Pak package is not recommended for Surface Mount Application.

Notes:

- ① Repetitive rating: $V_{GE}=20V$; pulse width limited by maximum junction temperature (figure 20)
- ② $V_{CC}=80\%(V_{CES})$, $V_{GE}=20V$, $L=10\mu H$, $R_G=50\Omega$ (figure 19)
- ③ Pulse width $\leq 80\mu s$; duty factor $\leq 0.1\%$.
- ④ Pulse width $5.0\mu s$, single shot.

Note: For the most current drawing please refer to IR website at <http://www.irf.com/package/>

Data and specifications subject to change without notice.

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Электрон
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